

ABSTRACT OF THE DISCLOSURE

In a nonvolatile memory, one or more peripheral transistor gates are formed from the same layer (140) as the select gate. The gate dielectric (130) for these peripheral transistors and the gate dielectric (130) for the select gates are formed simultaneously. In
5 a nonvolatile memory, the gate dielectric (130) for the peripheral transistors and the gate dielectric (130) for the select gates (140) have the same thickness. Portions of the control gates (170) overlie the select gates.